

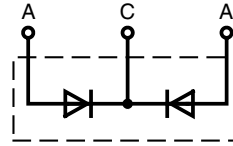
Common Cathode Fast Recovery Epitaxial Diode (FRED)

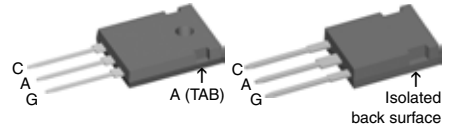
$$I_{FAVM} = 2 \times 34 \text{ A}$$

$$V_{RRM} = 200 \text{ V}$$

$$t_{rr} = 35 \text{ ns}$$

V_{RSM} V	V_{RRM} V	Type
200	200	DSEK 60-02A
200	200	DSEK 60-02AR


TO-247 AD
Version A

ISOPLUS247™
Version AR


A = Anode, C = Cathode, G = Gate

Symbol	Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	50	A
I_{FAVM} ①	$T_C = 115^\circ\text{C}$; rectangular, $d = 0.5$	34	A
I_{FRM}	$t_p < 10 \mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	375	
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	325	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	350	A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	290	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	310	A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	530	A ² s
	$t = 8.3 \text{ ms}$ (60 Hz), sine	510	A ² s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	420	A ² s
	$t = 8.3 \text{ ms}$ (60 Hz), sine	400	A ² s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+150	°C
P_{tot}	$T_C = 25^\circ\text{C}$	125	W
M_d	mounting torque (Version A only)	0.8...1.2	Nm
F_C	mounting force with clip	20...120	N
V_{ISOL}	50/60 Hz, RMS, $t = 1 \text{ min.}$, leads-to-tab (AR only)	2500	V~
Weight	typical	6	g

Features

- International standard package JEDEC TO-247 AD
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behavior
- Epoxy meets UL 94V-0
- Version AR isolated and UL registered E153432

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Conditions	Characteristic Values per leg		
		typ.	max.	
I_R ①	$T_{VJ} = 25^\circ\text{C}$		200	μA
	$T_{VJ} = 25^\circ\text{C}$		50	μA
	$T_{VJ} = 125^\circ\text{C}$		5	mA
V_F	$I_F = 30 \text{ A}$		0.85	V
	$T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$		1.10	V
V_{T0}	For power-loss calculations only		0.72	V
r_T	$T_{VJ} = T_{VJM}$		4.2	m Ω
R_{thJC}			1	K/W
R_{thCH}		0.25		K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 100 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	35	50	ns
I_{RM}	$V_R = 100 \text{ V}$; $I_F = 30 \text{ A}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $L < 0.05 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$	4	5	A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$
Data according to IEC 60747 refer to a single diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

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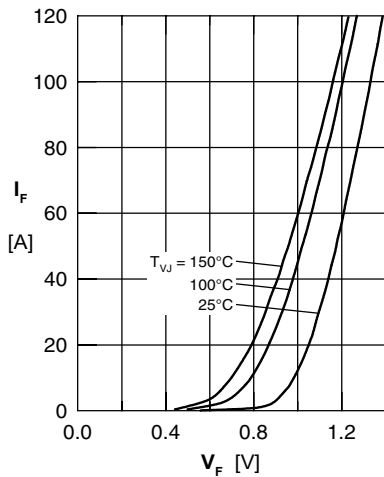


Fig. 1 Forward current I_F vs. V_F

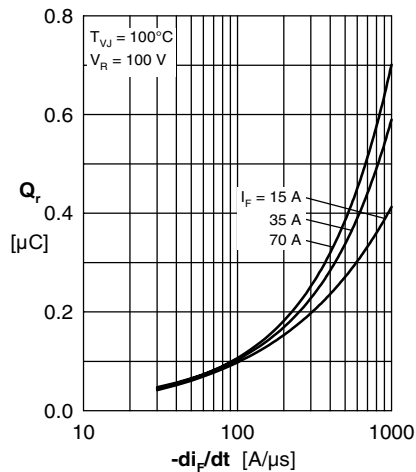


Fig. 2 Typ. reverse recov. charge Q_r

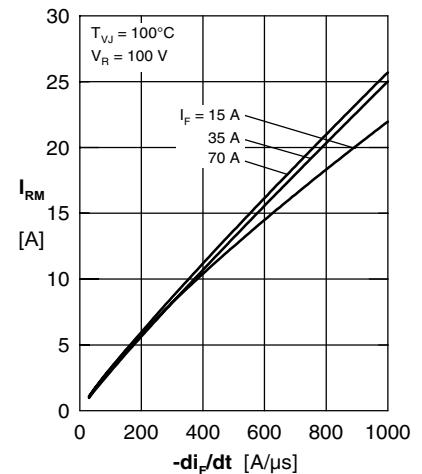


Fig. 3 Typ. peak reverse current I_{RM}

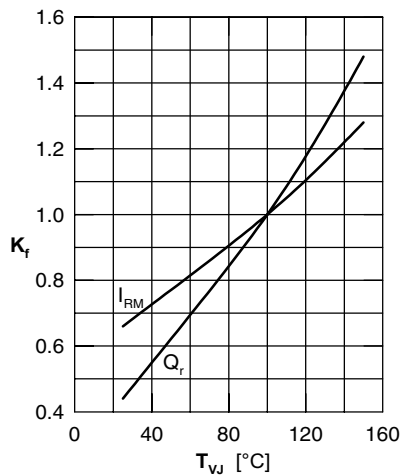


Fig. 4 Typ. dynamic parameters
 Q_r , I_{RM}

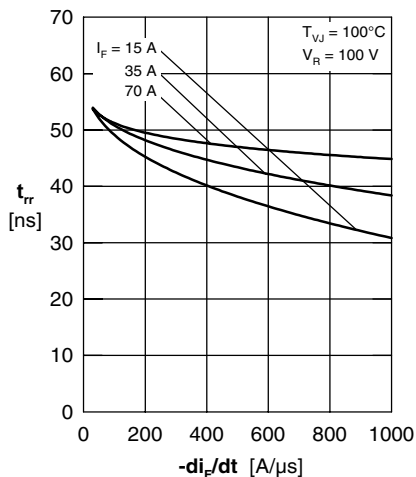


Fig. 5 Typ. recovery time
 t_{rr} vs. $-di_F/dt$

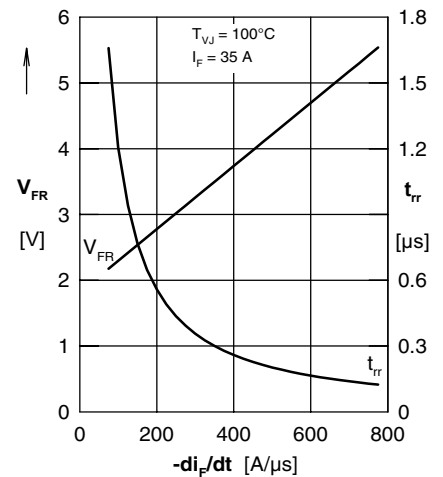


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{rr}

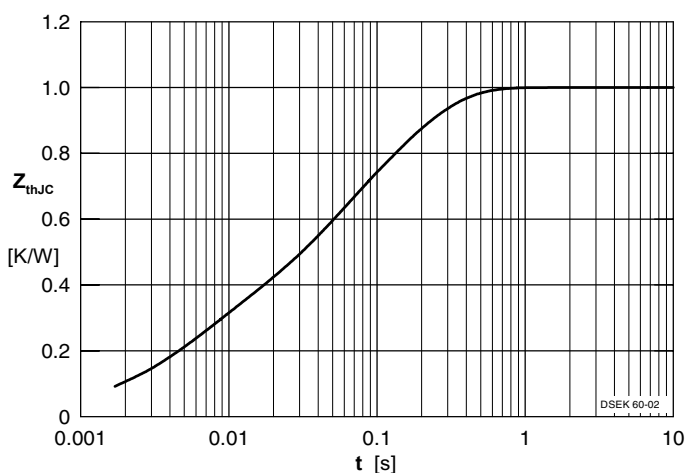
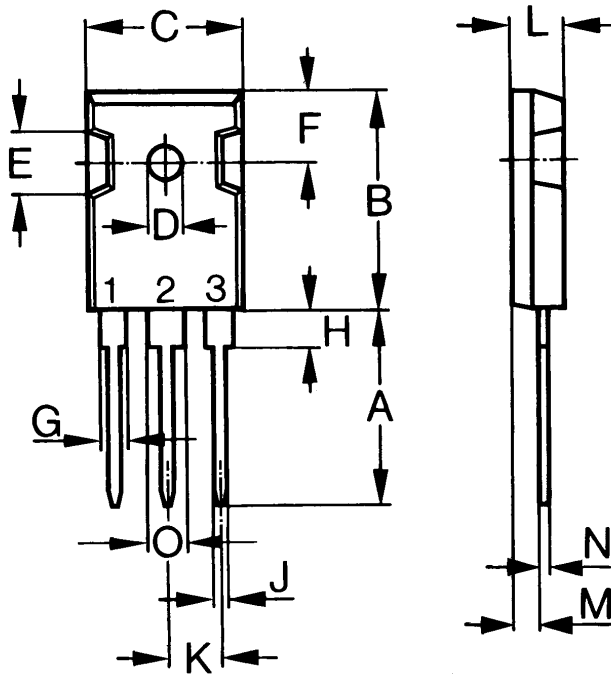
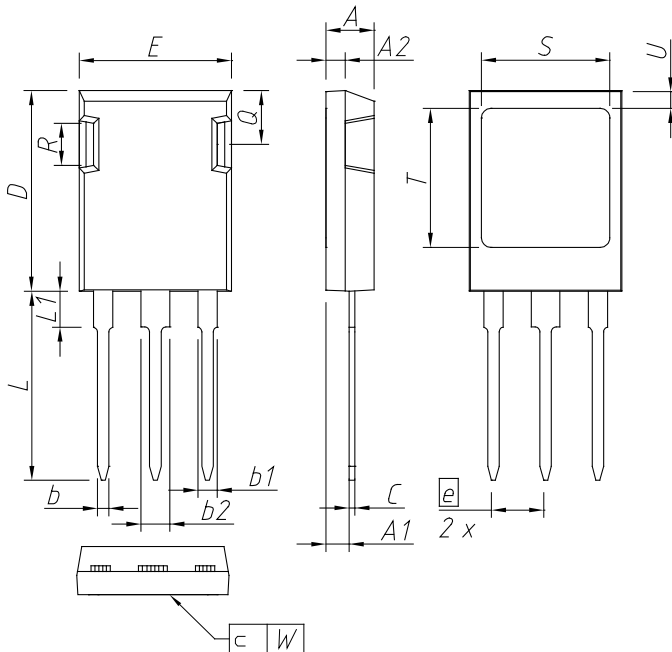


Fig. 7 Transient thermal resistance junction to case

TO-247 AD


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.20	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.50	-	0.177
J	1.00	1.40	0.040	0.055
K	10.80	11.00	0.426	0.433
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.087	0.102

ISOPLUS 247™


DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except Lmax.